

<b>Notice of References Cited</b>	Application/Control No. 10/776,823	Applicant(s)/Patent Under Reexamination HONG ET AL.	
	Examiner Steven H. Rao	Art Unit 2814	Page 1 of 1

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	C	US-6,762,126	07-2004	Cho et al.	438/694
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	V	Jung-Sik Choi et al., " A Shallow Trench Isolation using Novel Polysilazane-based SOG for Deep-Submicron Technologies and Beyond" IEEE 2003, 419-422
	W	Tsubaki JunIchiro, " Development of ceramic Nano-porous Materials" 2002, 167- 170.
	X	Tsali Cross et al. " Fabrication Process for Ultra High Aspect ratio Polysilazane- Derived MEMS " IEEE, 2002, 172-175.

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.